INFORMATION LETTER

Ministry of Higher Education, Science and Innovations of the Republic of Uzbekistan, Ministry of Energy of the Republic of Uzbekistan, Academy of Sciences of the Republic of Uzbekistan, Institute of Semiconductor Physics and Microelectronics at the National University of Uzbekistan, Branch of the Federal State Budgetary Educational Institution of Higher Education "National Research University "MPEI" in Tashkent and Tashkent State Technical University are jointly holding the III International Scientific Conference **“Modern trends in the development of semiconductor physics: achievements, problems and prospects”** on September 26-27, 2024.

The purpose of the conference: improving the quality of research work carried out by physicists of the Republic of Uzbekistan and promoting the implementation of results in production, as well as establishing scientific contacts between domestic and foreign scientists.

In this regard, we ask you to submit abstracts of reports electronically in Uzbek, Russian or English through the official conference website (https://journal.ispm.uz/conference/Anketa.html) before September 10, 2024.

Works in the following areas will be presented at the conference:

Section 1: Theoretical and experimental problems of semiconductor physics.

Section 2: Materials of semiconductor opto-, micro- and nanoelectronics, technologies and components.

Section 3: Creation of highly efficient technologies for the use of alternative energy sources and their development.

Section 4: Prospects for the development of traditional energy.

Section 5: Young scientists’ views on current problems in physics.

Requirements for formatting abstracts of reports are specified in the Appendix.

Publication of abstracts is free. Conference participants who made a presentation will receive an electronic certificate. The collection of conference materials will be available for downloading from the official website of the Institute of Semiconductor Physics and Microelectronics (www.ispm.uz) after the conference.

Based on the results of the conference, the best reports will be published in the form of an article in the scientific journal “Semiconductor Physics and Microelectronics” in accordance with its requirements.

The conference will begin at 10:00 on September 26, 2024. The online format will be implemented through the Zoom platform. A Zoom link will be sent to the email address participants provided upon registration.

Detailed information about the conference is available on the website: www.ispm.uz.

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APPENDIX

REQUIREMENTS FOR THE ABSTRACTS OF REPORTS

The text of the abstracts of the report should be written in Times New Roman, 14 pt, with a line spacing of 1.15. The volume of abstracts should not exceed 3 pages of A4 format (210 × 297 mm) with margins:

top - 20 mm;	left - 30 mm;
bottom - 20 mm;	right - 15 mm.

The title of the abstracts of the report is printed in capital (capital) letters in bold type. By adding an interval after the paragraph of the title, the initials and surnames of the authors are printed in bold type (the full name of the speaker is underlined).

From the next line, the name of the organization is printed in the main font for each of the authors, indicating the city and country.

The title of the abstracts of the report, the initials and surname of the authors, information about the organization are aligned in the center.

After the interval after the last line, the text of the abstracts of the report is printed in the main font. The main text should be justified, leaving a 1 cm indent in the first line of the paragraph.

By adding an interval after the main text, a list of references is provided according to the following model:

References

(for articles)

[1] Author(s). *Article title. Name of the journal. (Year), Number (or Volume (Number)), pp.1-10.*

(for books)

[2] Author(s). Surname(s). Name of the book. (City, Publisher, year)